

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Maximum Drain voltage ⁽¹⁾	V _{D,Max}	800	V
Drain-Gate voltage (R _{GS} =1MΩ)	V _{DGR}	800	V
Gate-source (GND) voltage	V _{GS}	±30	V
Drain current pulsed ⁽²⁾	I _{DM}	32.0	ADC
Single pulsed avalanche energy ⁽³⁾	E _{AS}	810	mJ
Avalanche current ⁽⁴⁾	I _{AS}	15	A
Continuous drain current (T _C =25°C)	I _D	8.0	ADC
Continuous drain current (T _C =100°C)	I _D	5.6	ADC
Maximum Supply voltage	V _{CC,MAX}	30	V
Input voltage range	V _{FB}	-0.3 to V _{SD}	V
Total power dissipation	P _D	190	W
	Derating	1.54	W/°C
Operating ambient temperature	T _A	-25 to +85	°C
Storage temperature	T _{STG}	-55 to +150	°C

Notes:

1. T_j=25°C to 150°C
2. Repetitive rating: Pulse width limited by maximum junction temperature
3. L=24mH, V_{DD}=50V, R_G=25Ω, starting T_j=25°C
4. L=13μH, starting T_j=25°C

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =50μA	800	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =Max., Rating, V _{GS} =0V	-	-	50	μA
		V _{DS} =0.8Max., Rating, V _{GS} =0V, T _C =125°C	-	-	200	μA
Static drain source on resistance ^(note)	R _{DS(ON)}	V _{GS} =10V, I _D =5.0A	-	1.2	1.5	Ω
Forward transconductance ^(note)	g _{fs}	V _{DS} =15V, I _D =5.0A	1.5	2.5	-	S
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V, f=1MHz	-	2460	-	pF
Output capacitance	C _{oss}		-	210	-	
Reverse transfer capacitance	C _{rss}		-	64	-	
Turn on delay time	t _{d(on)}	V _{DD} =0.5BV _{DSS} , I _D =8.0A (MOSFET switching time are essentially independent of operating temperature)	-	-	90	nS
Rise time	t _r		-	95	200	
Turn off delay time	t _{d(off)}		-	150	450	
Fall time	t _f		-	60	150	
Total gate charge (gate-source+gate-drain)	Q _g	V _{GS} =10V, I _D =8.0A, V _{DS} =0.5BV _{DSS} (MOSFET switching time are essentially independent of operating temperature)	-	-	150	nC
Gate source charge	Q _{gs}		-	20	-	
Gate drain (Miller) charge	Q _{gd}		-	70	-	

Note:

Pulse test: Pulse width ≤ 300μS, duty cycle ≤ 2%

$$S = \frac{1}{R}$$

Electrical Characteristics (CONTROL part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start threshold voltage	VSTART	-	14	15	16	V
Stop threshold voltage	VSTOP	After turn on	9	10	11	V
OSCILLATOR SECTION						
Initial accuracy	FOSC	KA1L0880B	45	50	55	kHz
		KA1M0880B	61	67	73	
Frequency change with temperature ⁽²⁾	$\Delta F/\Delta T$	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%
Maximum duty cycle	Dmax		74	77	80	%
FEEDBACK SECTION						
Feedback source current	IFB	Ta=25°C, 0V ≤ Vfb ≤ 3V	0.7	0.9	1.1	mA
Shutdown Feedback voltage	VSD	-	6.9	7.5	8.1	V
Shutdown delay current	Idelay	Ta=25°C, 5V ≤ Vfb ≤ VSD	4.0	5.0	6.0	μA
SOFT START SECTION						
Soft Start Voltage	VSS	VFB = 2V	4.7	5.0	5.3	V
Soft Start Current	ISS	Sync & S/S=GND	0.8	1.0	1.2	mA
REFERENCE SECTION						
Output voltage ⁽¹⁾	Vref	Ta=25°C	4.80	5.00	5.20	V
Temperature Stability ⁽¹⁾⁽²⁾	Vref/ΔT	-25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C
CURRENT LIMIT (SELF-PROTECTION) SECTION						
Peak Current Limit	I _{OVER}	Max. inductor current	4.40	5.00	5.60	A
PROTECTION SECTION						
Thermal shutdown temperature (Tj) ⁽¹⁾	TSD	-	140	160	-	°C
Over voltage protection voltage	VOVP	-	23	25	28	V
TOTAL DEVICE SECTION						
Start Up current	I _{START}	VCC=14V	0.1	0.3	0.45	mA
Operating supply current (control part only)	I _{OP}	Ta=25°C	6	12	18	mA
VCC zener voltage	VZ	ICC=20mA	30	32.5	35	V

Note:

1. These parameters, although guaranteed, are not 100% tested in production
2. These parameters, although guaranteed, are tested in EDS (wafer test) process

Typical Performance Characteristics

(These characteristic graphs are normalized at $T_a=25^\circ\text{C}$)

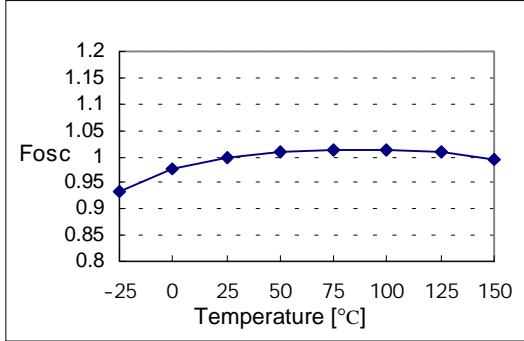


Figure 1. Operating Frequency

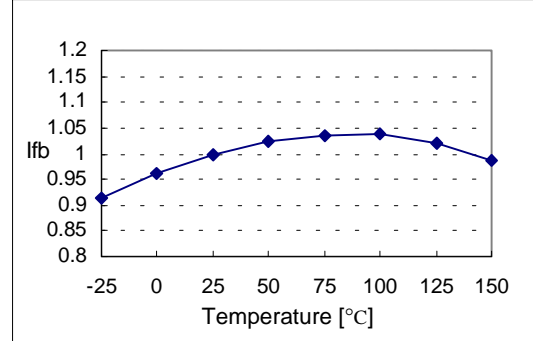


Figure 2. Feedback Source Current

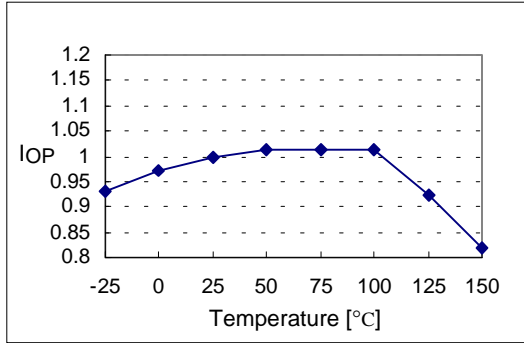


Figure 3. Operating Supply Current

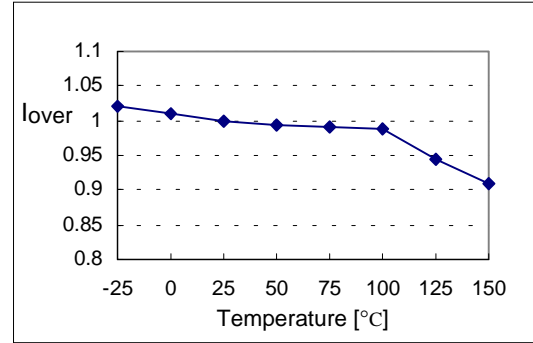


Figure 4. Peak Current Limit

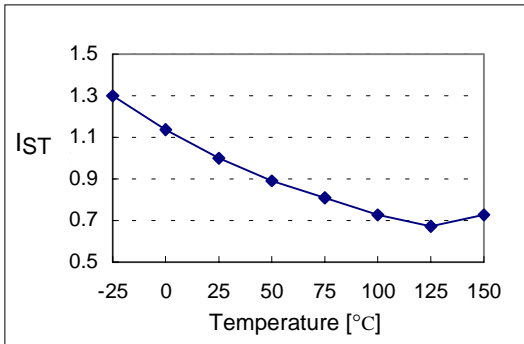


Figure 5. Start up Current

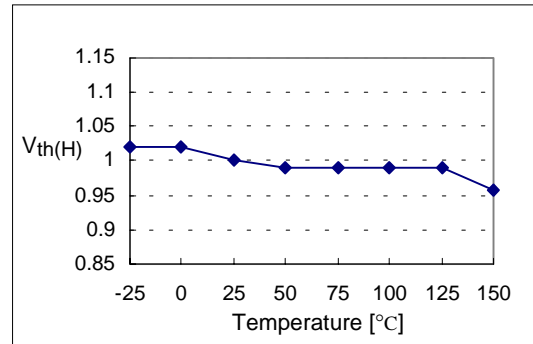


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at $T_a=25^\circ\text{C}$)



Figure 7. Stop Threshold Voltage



Figure 8. Maximum Duty Cycle



Figure 9. VCC Zener Voltage



Figure 10. Shutdown Feedback Voltage



Figure 11. Shutdown Delay Current



Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at $T_a=25^\circ\text{C}$)

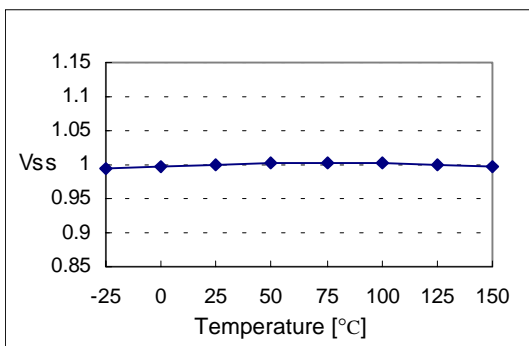


Figure 13. Soft Start Voltage

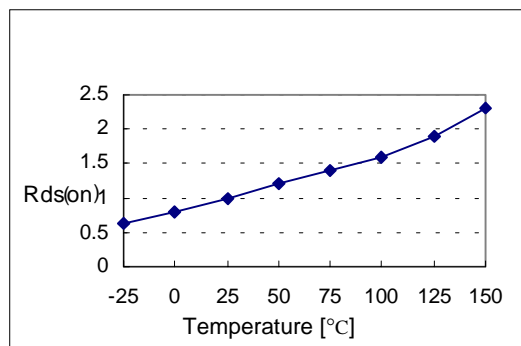


Figure 14. Static Drain Source on Resistance

Package Dimensions

TO-3P-5L



Ordering Information

Product Number	Package	Rating	Fosc
KA1L0880B-TU	TO-3P-5L	800V, 8A	50kHz
KA1L0880B-YDTU	TO-3P-5L(Forming)		
KA1M0880B-TU	TO-3P-5L	800V, 8A	67kHz
KA1M0880B-YDTU	TO-3P-5L(Forming)		

TU : Non Forming Type

YDTU : Forming type

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